12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20251203001.2
Qualification of RFAB using qualified Process Technology, Probe site Die Revision, Datasheet, and Assembly/Test site (CDAT) for select devices
Change Notification / Sample Request

Date: December 04, 2025
To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments (TI). The details of this change are on the following pages, and are in alignment with our standard product change notification (PCN) process.

TI requires acknowledgement of receipt of this notification within 60 days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 60 days of this notification, given that samples are not built ahead of the change.

The Proposed First Ship date in this PCN letter is the earliest possible date that customers could receive the changed material. It is our commitment that the changed device will not ship before that date. If samples are requested within the 60 day sample request window, customers will still have 30-days to complete their evaluation regardless of the proposed 1st ship date.

As referenced in the "reason for change" below, this particular PCN relates to TI's multiyear transition, announced in 2020, to close our 150mm production and move more capacity into 300mm. We are entering the final phases of this transition, and the final 150mm wafers started in October 2025. **Thus, it's critical that you take the appropriate actions, noted in this PCN, to prepare for applicable product changes.**

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the Change Management team. For sample requests or sample related questions, contact your local Field Sales Representative. As always, we thank you for your continued business.

Change Management Team
SC Business Services

20251203001.2
Attachment:

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records**,** you have recently purchased these devices**.** The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
TPS73733QDRBRQ1	TPS73733QDRBRQ1

Technical details of this Product Change follow on the next page(s).

PCN Number:	20251203001.2	PCN Date:	December 04, 2025
Title:	Qualification of RFAB using qualified Process Technology, Probe site, Die Revision, Datasheet, and Assembly/Test site (CDAT) for select devices		
Customer Contact:	Change Management Team	Dept:	Quality Services
Proposed 1st Ship Date:	June 02, 2026	Sample requests accepted until:	February 02, 2026*

***Sample requests received after February 02, 2026 will not be supported.**

Change Type:		
☒ Assembly Site	☒ Design	☐ Wafer Bump Material
☒ Assembly Process	☒ Data Sheet	☐ Wafer Bump Process
☒ Assembly Materials	☐ Part number change	☒ Wafer Fab Site
☐ Mechanical Specification	☒ Test Site	☒ Wafer Fab Materials
☒ Packing/Shipping/Labeling	☐ Test Process	☒ Wafer Fab Process

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab option for the devices listed below as well as new assembly/Test site (CDAT) options:

Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
DFAB	LBC4	150 mm	RFAB	LBC9	300 mm

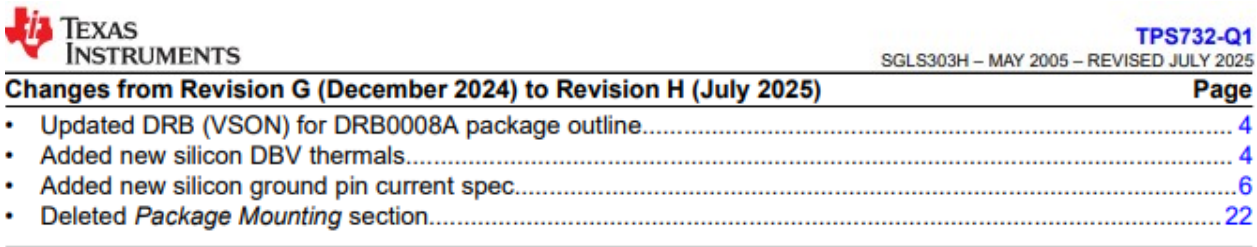
The die was also changed as a result of the process change.

	Current	New
Probe Site	DMOS4	CD-PR

Construction differences are as follows:

	Current Site	Additional Site
Assembly/Test Site	MLA	CDAT
Wire diam/type	1.3 mil Cu	1 mil Cu
Mold Compound	4208625	4222198
Mount Compound	4207123	4225839
Final Wafer Thickness	254um	190um
MSL	3	1

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The links to the revised datasheets are available in the table below.



TEXAS INSTRUMENTS

TPS732-Q1

SGLS303H – MAY 2005 – REVISED JULY 2025

Changes from Revision G (December 2024) to Revision H (July 2025) **Page**

- Updated DRB (VSON) for DRB0008A package outline..... 4
- Added new silicon DBV thermals..... 4
- Added new silicon ground pin current spec..... 6
- Deleted *Package Mounting* section..... 22

Changes from Revision B (September 2019) to Revision C (March 2025) **Page**

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
TPS732-Q1	SGLS303G	**SGLS303H**	http://www.ti.com/product/TPS732-Q1
TPS737-Q1	SBVS123B	**SBVS123C**	http://www.ti.com/product/TPS737-Q1

Changes between new and legacy devices are labeled in the datasheet as legacy silicon (LBC4) and new silicon (LBC9), respectively. An example of that comparison for TPS736-Q1 is shown below:

5.6 Electrical Characteristics

Over operating temperature range (T_J = –40°C to 125°C), V_{IN} = $V_{OUT(nom)}$ + 0.5V(1) , I_{OUT} = 10mA, V_{EN} = 1.7V, and C_{OUT} = 0.1µF (unless otherwise noted). Typical values are at T_J = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{GND}	Ground pin current	I_{OUT} = 10mA (I_Q), legacy silicon		400	550	µA
		I_{OUT} = 10mA (I_Q), new silicon		400	630	

8.1.1 Device Nomenclature

Table 8-1. Ordering Information

PRODUCT	DESCRIPTION(1)
TPS732**xx**Q**yyyz**(M3)Q1	**xx** is the nominal output voltage (for example, 25 = 2.5 V, 01 = Adjustable (2)). **Q** indicates that the device is a grade-1 device in accordance with the AEC-Q100 standard. **yyy** is the package designator. **z** is the package quantity. **M3** is a suffix designator for devices that only use the latest manufacturing flow (CSO: RFB). Devices without this suffix can ship with the *legacy silicon* (CSO: DLN) or the *new silicon* (CSO: RFB). The reel packaging label provides CSO information to distinguish which silicon is being used. Device performance for new and legacy silicon is denoted throughout the document. **Q1** indicates that this device is an automotive grade (AEC-Q100) device.

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the device product folder at www.ti.com.
(2) For fixed 1.20V operation, tie FB to OUT.

Qual details are provided in the Qual Data Section.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

Any differences/changes between the LBC4 die and LBC9 die have been made in the data sheet using “Legacy silicon” (LBC4) and “New silicon” (LBC9).

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DFAB	DLN	USA	Dallas
RFAB	**RFB**	**USA**	**Richardson**

Die Rev:

Current	New
Die Rev [2P]	**Die Rev [2P]**
A	**A**

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
MLA	MLA	MYS	KUALA LUMPUR
CDAT	**CDA**	**CHN**	**Chengdu**

Sample product shipping label (not actual product label)

Product Affected:

TPS73201QDRBRQ1	TPS73733QDRBRQ1		

For alternate parts with similar or improved performance, please visit the product page on TI.com

Product Attributes

Attributes	Qual Device: TPS73733QDRBRM3Q1	QBS Package Reference: CAXC8T245QRHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Process, Product Reference: TPS73701QDCQRM3Q1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Logic	Power Management	Power Management
Wafer Fab Supplier	RFAB	MH8	RFAB	RFAB
Assembly Site	CDAT	CDAT	MLA	TFME
Package Group	QFN	QFN	TSSOP	SOT
Package Designator	DRB	RHL	PW	DCQ
Pin Count	8	24	16	6

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device TPS73733QDRBRM3Q1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS73733QDRBRM3Q1	QBS Package Reference: CAXC8T245QRHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Process, Product Reference: TPS73701QDCQRM3Q1
Test Group A - Accelerated Environment Stress Tests											
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/All Pass	3/All Pass	-	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	-	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-	-	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	-	-
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	3/36/0	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/45/0	3/135/0	-	-
Test Group B - Accelerated Lifetime Simulation Tests											
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	-	3/231/0	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-
EDR	B3	AEC Q100-005	1	77	NVM Endurance, Data Retention, and Op Life	Per QSS-009-018	1 Step	1/77/0	-	3/231/0	1/77/0
Test Group C - Package Assembly Integrity Tests											

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS73733QDRBRM3Q1	QBS Package Reference: CAXC8T245QRHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Process, Product Reference: TPS73701QDCQRM3Q1
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/30/0	3/30/0	-	-
Test Group D - Die Fabrication Reliability Tests											
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests											
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	-	-	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	-	-	1/3/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS73733QDRBRM3Q1	QBS Package Reference: CAXC8T245QRHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Process, Product Reference: TPS73701QDCQRM3Q1
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	1/6/0	-	-	1/12/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	-	-	3/90/0
Additional Tests											

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2402-053

ZVEI IDs: SEM-DE-01, SEM-DE-02, SEM-DE-03, SEM-DS-01, SEM-DS-02, SEM-DS-03, SEM-PW-02, SEM-PW-09, SEM-PW-13, SEM-PA-03, SEM-PA-05, SEM-PA-07, SEM-PA-08, SEM-PA-11, SEM-PA-14, SEM-PA-17, SEM-PA-13, SEM-PA-18, SEM-PS-02, SEM-TF-01, SEM-PA-03, SEM-BD-01

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.